

New Jersey Semi-Conductor Products, Inc.

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SPRINGFIELD, NEW JERSEY 07081
U.S.A.

TELEPHONE: (973) 376-2922
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2N6040 thru 2N6042 PNP
2N6043 thru 2N6045 NPN
MJE6040 thru MJE6041 PNP
MJE6043 thru MJE6045 NPN

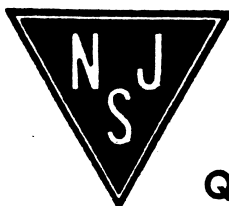
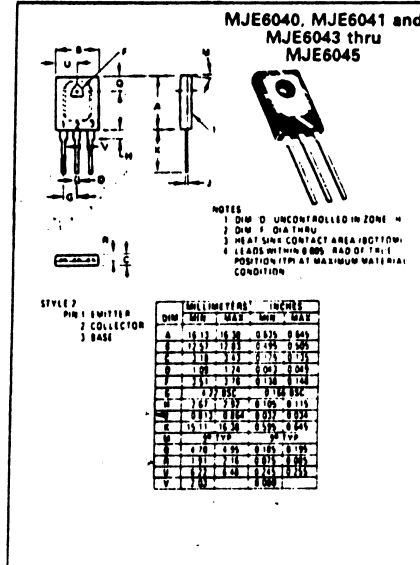
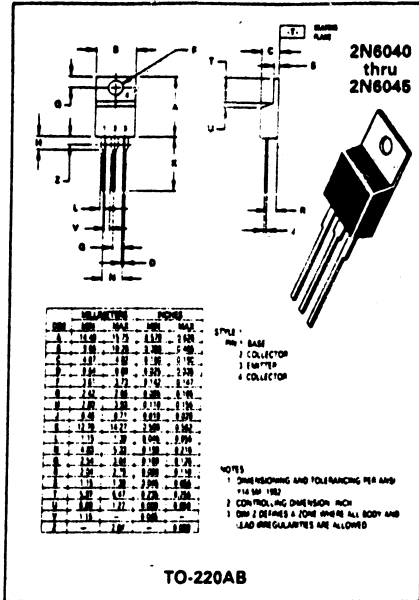
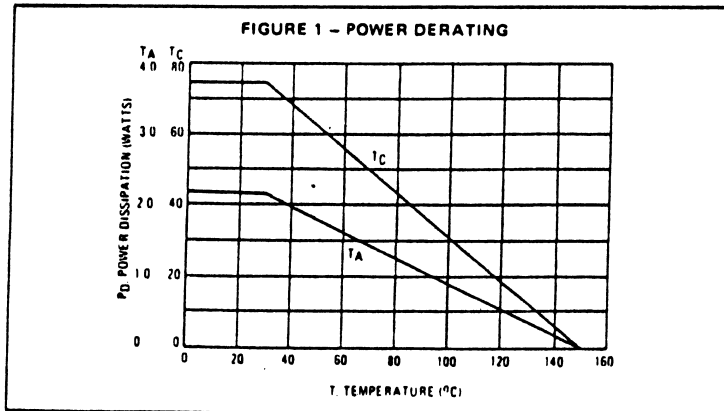
***MAXIMUM RATINGS**

Rating	Symbol	2N6040	2N6041	2N6042	Unit
		2N6043 MJE6040	2N6044 MJE6041	2N6045 MJE6045	
Collector-Emitter Voltage	V _{CEO}	60	80	100	V _{d.c.}
Collector-Base Voltage	V _{CB}	60	80	100	V _{d.c.}
Emitter-Base Voltage	V _{EB}	← 5.0 →			V _{d.c.}
Collector Current - Continuous Peak	I _C	← 8.0 →			A _{d.c.}
		← 16 →			
Base Current	I _B	← 120 →			mA _{d.c.}
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	← 75 →			Watts
		← 0.60 →			
Total Power Dissipation @ T _A = 25°C Derate above 25°C	P _D	← 2.2 →			Watts
		← 0.0175 →			
Operating and Storage Junction Temperature Range	T _J , T _{stg}	← -65 to +150 →			°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	θ _{JC}	1.67	°C/W
Thermal Resistance, Junction to Ambient	θ _{JA}	57	°C/W

*Indicates JEDEC Registered Data



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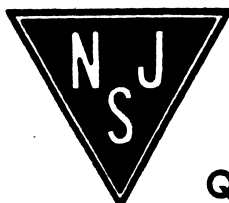
TELEPHONE: (973) 376-2922
 (212) 227-6000
 FAX: (973) 376-8966

2N6040 thru 2N6042 PNP
2N6043 thru 2N6045 NPN
MJE6040 thru MJE6041 PNP
MJE6043 thru MJE6045 NPN

***ELECTRICAL CHARACTERISTICS** (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Sustaining Voltage (I _C = 100 mA, I _B = 0)	V _{CE(sus)}	80 80 100	- - -	V _{dc}
Collector Cutoff Current (V _{CE} = 80 Vdc, I _B = 0) (V _{CE} = 80 Vdc, I _B = 0) (V _{CE} = 100 Vdc, I _B = 0)	I _{CEO}	- - -	20 20 20	μA
Collector Cutoff Current (V _{CE} = 60 Vdc, V _{BE(off)} = 1.5 Vdc) (V _{CE} = 80 Vdc, V _{BE(off)} = 1.5 Vdc) (V _{CE} = 100 Vdc, V _{BE(off)} = 1.5 Vdc) (V _{CE} = 60 Vdc, V _{BE(off)} = 1.5 Vdc, T _C = 150°C) (V _{CE} = 80 Vdc, V _{BE(off)} = 1.5 Vdc, T _C = 150°C) (V _{CE} = 100 Vdc, V _{BE(off)} = 1.5 Vdc, T _C = 150°C)	I _{CEx}	- - - - - -	20 20 20 200 200 200	μA
Collector Cutoff Current (V _{CB} = 80 Vdc, I _E = 0) (V _{CB} = 80 Vdc, I _E = 0) (V _{CB} = 100 Vdc, I _E = 0)	I _{CBO}	- - -	20 20 20	μA
Emitter Cutoff Current (V _{BE} = 5.0 Vdc, I _C = 0)	I _{EBO}	-	2.0	mA
ON CHARACTERISTICS				
DC Current Gain (I _C = 4.0 A, V _{CE} = 4.0 Vdc) 2N6040, 41, 2N6043, 44, MJE6040, 41, MJE6043, 44 (I _C = 3.0 A, V _{CE} = 4.0 Vdc) 2N6042, 2N6045, MJE6045 (I _C = 8.0 A, V _{CE} = 4.0 Vdc) All Types	h _{FE}	1000 1000 100	20,000 20,000 -	-
Collector-Emitter Saturation Voltage (I _C = 4.0 A, I _B = 16 mA) 2N6040, 41, 2N6043, 44, MJE6040, 41, MJE6043, 44 (I _C = 3.0 A, I _B = 12 mA) 2N6042, 2N6045, MJE6045 (I _C = 8.0 A, I _B = 80 mA) All Types	V _{CE(sat)}	- - -	2.0 2.0 4.0	V _{dc}
Base-Emitter Saturation Voltage (I _C = 8.0 A, I _B = 80 mA)	V _{BE(sat)}	-	4.5	V _{dc}
Base-Emitter On Voltage (I _C = 4.0 A, V _{CE} = 4.0 Vdc)	V _{BE(on)}	-	2.8	V _{dc}
DYNAMIC CHARACTERISTICS				
Small-Signal Current Gain (I _C = 3.0 A, V _{CE} = 4.0 Vdc, f = 10 MHz)	h _{fe}	40	-	-
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0.1 + 0.1 MHz)	C _{ob}	- -	300 200	pF
Small-Signal Current Gain (I _C = 3.0 A, V _{CE} = 4.0 Vdc, f = 1.0 kHz)	h _{fe}	300	-	-

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